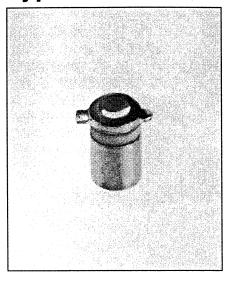
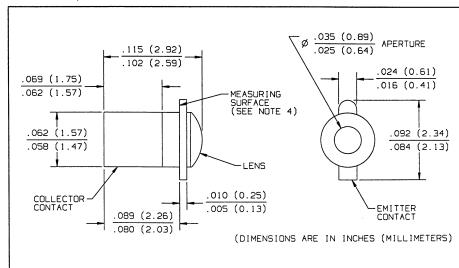


# NPN Silicon Phototransistors Types OP600A, OP600B, OP600C





#### **Features**

- · Narrow receiving angle
- Variety of sensitivity ranges
- Enhanced temperature range
- · Ideal for direct mounting in PC boards
- Mechanically and spectrally matched to the OP123 and OP223 series devices
- TX/TXV processing available (see Hi-Rel section)

#### Description

The OP600 series device consists of an NPN silicon phototransistor mounted in a hermetically sealed "Pill" type package. The narrow receiving angle provides excellent on-axis coupling. These devices are 100% production tested using infrared light for close correlation with Optek GaAs and GaAlAs emitters.

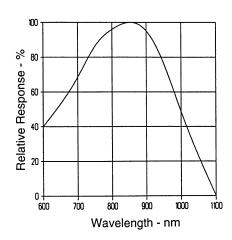
## **Absolute Maximum Ratings** (T<sub>A</sub> = 25° C unless otherwise noted)

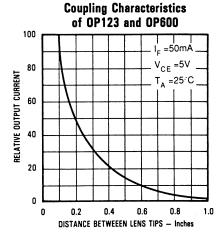
Collector-Emitter Voltage
Emitter-Collector Voltage 5.0 V
Storage Temperature Range
Operating Temperature Range65° C to +125° C
Soldering Temperature (5 sec. with soldering iron)
Power Dissipation
Continuous Collector Current 50 mA
Notes:

- (1) Refer to Application Bulletin 202 which discusses proper techniques for soldering Pill type devices to PC boards.
- (2) No clean or low solids, RMA flux is recommended. Duration can be extended to 10 sec. max. when flow soldering.
- (3) Derate linearly 0.5mW/° C above 25° C.
- (4) Junction temperature maintained at 25° C.
- (5) Light source is a GaAlAs LED, peak Wavelength = 890 nm, providing an irradiance of 2.5 mW/cm<sup>2</sup>. The source irradiance is not necessarily uniform over the entire lens area of the unit under test.

### **Typical Performance Curves**

#### **Typical Spectral Response**



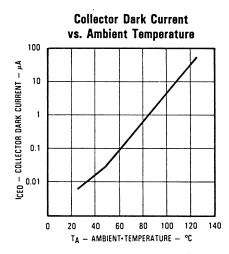


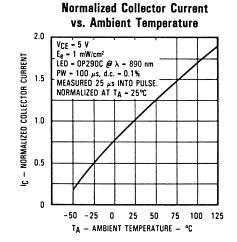
## Types OP600A, OP600B, OP600C

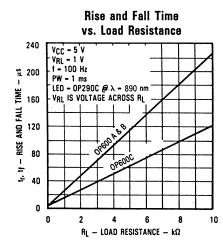
Electrical Characteristics (T<sub>A</sub> = 25° C unless otherwise noted)

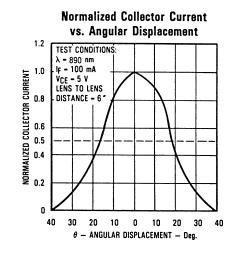
SYMBOL	PARAMETER		MIN	TYP	MAX	UNITS	TEST CONDITIONS
I <sub>C(ON)</sub> <sup>(4)</sup>	On-State Collector Current	OP600C OP600B OP600A	0.30 0.60 1.20		1.8	mA mA mA	$V_{CE} = 5 \text{ V, } E_e = 2.5 \text{ mW/cm}^{2(5)}$
ICEO	Collector Dark Current					nA	V <sub>CE</sub> = 10 V, E <sub>e</sub> = 0
V <sub>(BR)</sub> CEO	Collector-Emitter Breakdown Voltage		25			٧	I <sub>C</sub> = 100 μA
V <sub>(BR)ECO</sub>	Emitter-Collector Breakdown Voltage		5.0			٧	I <sub>E</sub> = 100 μA
VCE(SAT) <sup>(4)</sup>	Collector-Emitter Saturation Voltage				0.40	٧	$I_C = 0.15 \text{ mA}, E_e = 2.5 \text{ mW/cm}^{2(5)}$
t <sub>r</sub>	Rise Time Fall Time			15 15		μs μs	$V_{CC}$ = 5 V, $I_C$ = 0.80 mA, $R_L$ = 1 k $\Omega$ , See Test Circuit

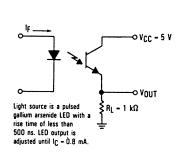
### **Typical Performance Curves**











**Switching Time** 

**Test Circuit** 

## **X-ON Electronics**

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Phototransistors category:

Click to view products by TT Electronics manufacturer:

Other Similar products are found below:

LTR-5576D PT17-21B/L41/TR8 PT908-7B-F ASDL-6620-C22 OED-ST-8LR2 OED-STR44B90-TR SD5410-109 PT26-21C/CT PT15-21B-TR8 PT-IC-AC-3528-520 PT-IC-BC-3528-550 MHT153PTBT MHS153PTBT PT5529B/L2/H2-F PT91-21C/TR10 BP 103-3/4 BPX 38-3 BPY 62 KPS-3227SP1C L-53P3BT L-53P3C L-93DP3BT L-93DP3C LL-503PTC2E-1AD LL-S150PTC-1A LL-S150PTD-1A SFH 320 SFH 320-3 SFH 320 FA OP508FA TEMT1030 LTR-301 PGM5516-MP PGM5537-MP PGM5549 PGM5549-MP PGM5637D PGM5639D VTT7125H VEMT4700F-GS08 PT19-21B/L41/TR8 KP-2012P3C TEKT5400S SD1410-128L SFH 313 FA-3/4 SFH 313 FA-2/3 SFH 320-4-Z SFH 309 FA-5/6 PT4800FE000F SFH 309-5/6